Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	"5277748".pn. and (device near2 layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 19:42
L2	7	"6774010"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 21:24
L3	13	("5374564" | "5399231" | "5528397" | "5674758" | "5710057" | "5856229" | "5876497" | "5877034" | "5882987" | "5886078" | "5906951" | "5994207" | "6033974").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/10/16 19:49
L4	18	2 3	US-PGPUB; USPAT; USOCR	OR	ON	2005/10/16 19:49
L5	18	4 and thickness	US-PGPUB; USPAT; USOCR	OR	ON	2005/10/16 19:49
L6	60	((porous (porous near3 silicon)) with (substrate wafer) with (silicon near1 layer)) same ((support temporary) near1 (substrate layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 20:30
L7	176821	"438"/$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 20:05
L8	329028	"257"/$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 20:05
L9	401389	7 8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 20:06

L10	44	6 and 9	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 20:06
L11	23	(US-20050070048-$ or US-20050059221-$).did. or (US-4878991-$ or US-5250843-$ or US-5366573-$ or US-5841193-$ or US-6159767-$ or US-6911380-$ or US-6774010-$ or US-6649492-$ or US-6387829-$ or US-6255731-$ or US-6246068-$ or US-6143628-$ or US-6107213-$ or US-5854123-$ or US-5405802-$ or US-5277748-$ or US-6911375-$ or US-6881650-$ or US-5882987-$ or US-5876497-$ or US-5856229-$).did.	US-PGPUB; USPAT	OR	ON	2005/10/16 20:06
L12	40	10 not 11	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 20:06
L13	261	(silicon near1 layer) with (device near2 layer) with thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 20:31
L14	11	13 and porous	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 20:34
L15	250	13 not 14	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 20:34
L16	160	15 and 9	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 20:34

L17	28	(US-20050070048-$ or US-20050059221-$).did. or (US-4878991-$ or US-5250843-$ or US-5366573-$ or US-5841193-$ or US-6159767-$ or US-6911380-$ or US-6774010-$ or US-6649492-$ or US-6387829-$ or US-6255731-$ or US-6246068-$ or US-6143628-$ or US-6107213-$ or US-5854123-$ or US-5405802-$ or US-5277748-$ or US-6911375-$ or US-6881650-$ or US-5882987-$ or US-5876497-$ or US-5856229-$ or US-6881644-$ or US-6468841-$ or US-6375738-$ or US-5670411-$ or US-5453394-$).did.	US-PGPUB; USPAT	OR	ON	2005/10/16 20:59
L18	5	17 and (heat near1 sink)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 21:40
L19	2	17 and (heat near1 spreader)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 21:22
L20	1	2 and anodization	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 21:27
L21	14	17 and anodization	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 21:27
L22	13	17 and ((porous near1 silicon) with anodization)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 21:28
L23	50	"6323108"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 21:41

L24	2	"6323108".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/16 21:41